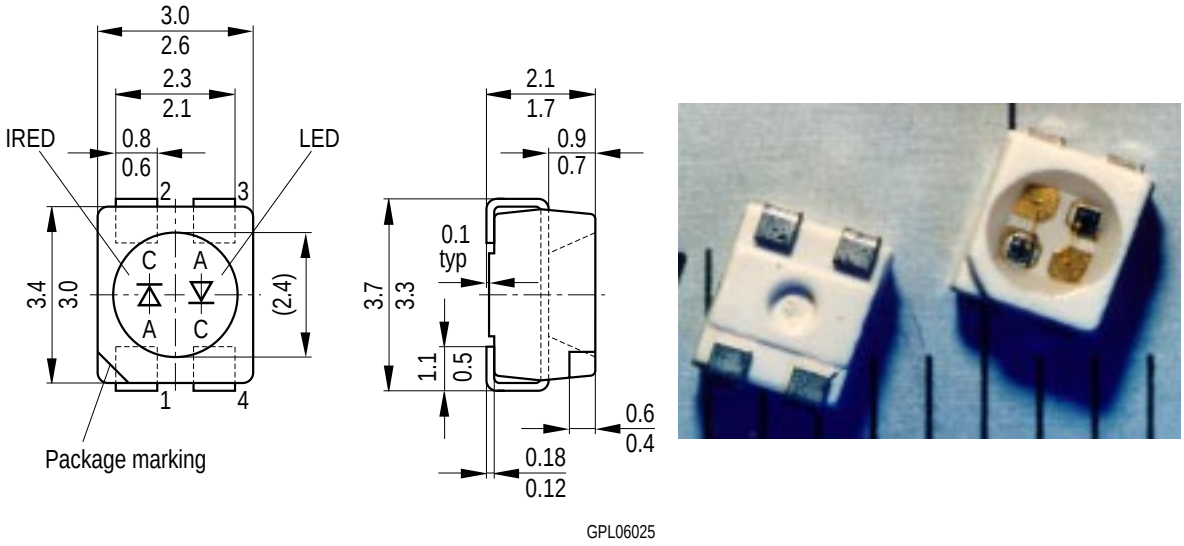
SIEMENS

SMT Multi TOPLED® SFH 7222

GaAlAs-IR-Lumineszenzdiode (880 nm) und grüne GaP-LED (565 nm)
GaAlAs-Infrared-Emitter (880 nm) and green GaP-LED (565 nm)



Maβe in mm, wenn nicht anders angegeben/Dimensions in mm, unless otherwise specified.

Wesentliche Merkmale

- Geeignet für Vapor-Phase Löten und IR-Reflow Löten
- Geeignet für SMT-Bestückung
- Gegurtet lieferbar
- Beide Sendedioden getrennt ansteuerbar

Features

- Suitable for vapor-phase and IR-reflow soldering
- Suitable for surface mount assembly
- Available taped on reel
- Both emitting diodes can be controlled separately

Anwendungen

- Infrarotanwendungen mit optischem Indikator

Applications

- IR-applications combined with optical indicator

Grenzwerte
Maximum Ratings

Bezeichnung **Description**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		IRED	**LED**	
Betriebstemperatur Operating temperature range	T_{op}	– 40 ... + 100	– 40 ... + 100	˚C
Lagertemperatur Storage temperature range	T_{stg}	– 40 ... + 100	– 40 ... + 100	˚C
Sperrspannung Reverse voltage	V_R	5	5	V
Durchlaßstrom Forward current	I_F (DC)	100	30	mA
Stoßstrom Surge current $t_p \leq 10$ µs, $D = 0$	I_{FSM}	2.5	0.5	A
Verlustleistung Total power dissipation	P_{tot}	180	100	mW
Wärmewiderstand Thermal resistance junction/ambient[1)]	$R_{th\ JA}$	450	500	K/W
Wärmewiderstand Thermal resistance junction/ambient[2)]	$R_{th\ JA}$	650		K/W

1) nur ein Chip betrieben
1) only one chip on

2) beide Chips betrieben
2) both chips on

Hinweis/Notes

Die angegebenen Grenzdaten gelten für einen Chip, wenn nicht anders angegeben.
The stated maximum ratings refer to one chip, unless otherwise specified.

Kennwerte (T_A = 25 ˚C)
Characteristics

Bezeichnung **Description**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		IRED	**LED**	
Wellenlänge der Strahlung Wavelength of peak emission I_F = 100 mA	λ_{peak}	880	565 (I_F = 10 mA)	nm
Dominantwellenlänge Dominant wavelength I_F = 10 mA	λ_{dom}	–	570	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} I_F = 100 mA	$\Delta\lambda$	80	25 (I_F = 10 mA)	nm
Abstrahlwinkel Half angle	φ	± 60	± 60	Grad deg.
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.4 × 0.4	0.25 × 0.25	mm^2
Schaltzeiten Switching times 10%/90%, I_F = 100 mA, R_L = 50 Ω	t_r, t_f	500	450, 200	ns
Kapazität Capacitance V_R = 0 V, f = 1 MHz	C_o	25	15	pF
Durchlaβspannung Forward voltage I_F = 10 mA I_F = 100 mA, t_p = 20 ms I_F = 1 A, t_p = 100 µs	V_F	 – 1.5 (≤ 1.8) 3.0 (≤ 3.8)	 2.0 (≤ 2.6) – –	V
Sperrstrom, V_R = 5 V Reverse current	I_R	0.01 (≤ 1)	0.01 (≤ 10)	µA
Gesamtstrahlungsfluβ Total radiant flux I_F = 100 mA, t_p = 20 ms	Φ_e	23	–	mW
Lichtstärke Luminous intensity I_F = 2 mA	I_V	–	8 (> 4)	mcd

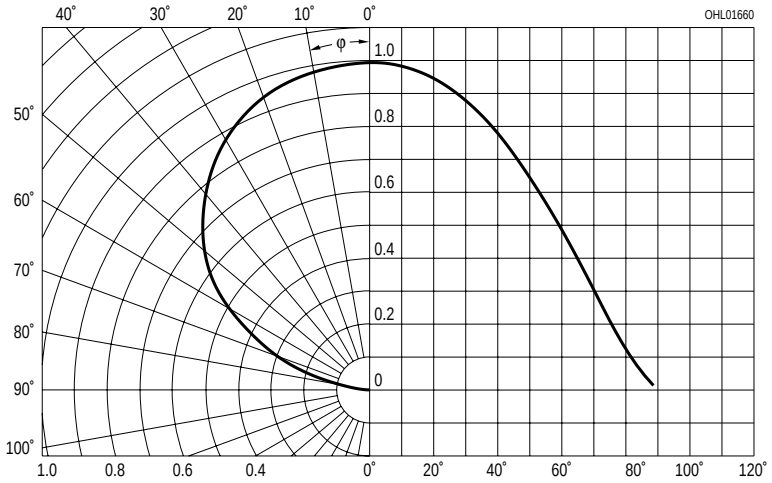
Kennwerte (T_A = 25 ˚C)
Characteristics

Bezeichnung **Description**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		IRED	**LED**	
Temperaturkoeffizient von I_e bzw. Φ_e Temperature coefficient of I_e or Φ_e I_F = 100 mA	TC_I	– 0.5	– 0.3	%/K
Temperaturkoeffizient von V_F Temperature coefficient of V_F I_F = 100 mA	TC_V	– 2	– 1.4	mV/K
Temperaturkoeffizient von λ Temperature coefficient of λ I_F = 100 mA	TC_λ	+ 0.25	$0.3 \times \lambda_{peak}$ $0.07 \times \lambda_{dom}$	nm/K

Strahlstärke I_e der IRED in Achsrichtung
gemessen bei einem Raumwinkel Ω = 0.01 sr
Radiant intensity I_e of the IRED in axial direction
at a solid angle of Ω = 0.01 sr

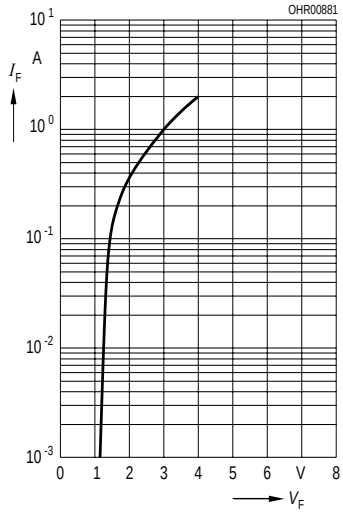
Bezeichnung **Description**	**Symbol** **Symbol**	**Werte** **Values**	**Einheit** **Unit**
Strahlstärke Radiant intensity I_F = 100 mA, t_p = 20 ms	$I_{e\ min.}$	≥ 4	mW/sr
Strahlstärke Radiant intensity I_F = 1 A, t_p = 100 µs	$I_{e\ typ.}$	48	mW/sr

IRED Radiation characteristics $I_{rel} = f(\varphi)$
LED Directional characteristics $S_{rel} = f(\varphi)$

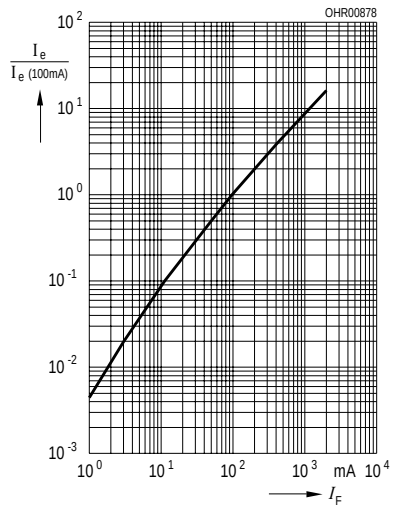


IRED

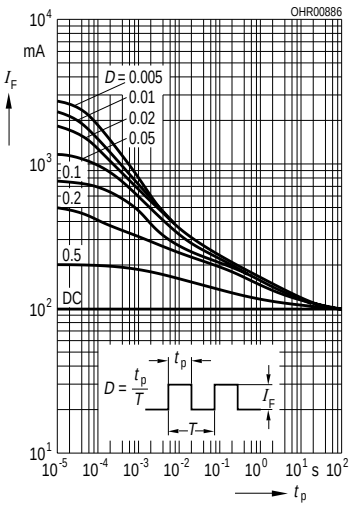
Forward current $I_F = f(V_F)$
T_A = 25 ˚C



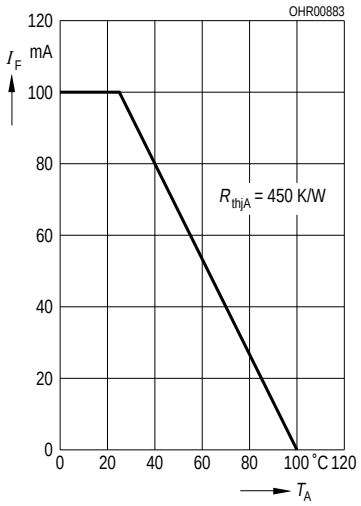
Rel luminous intensity $I_V / I_{V(10\ mA)} = f(I_F)$
T_A = 25 ˚C



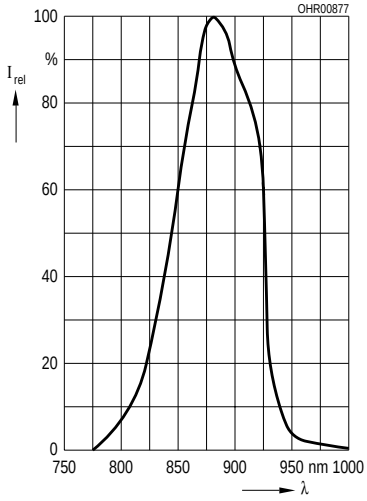
Perm. pulse handling capability $I_F = f(t_p)$
Duty cycle D = parameter, T_A = 25 ˚C



Max. permissible forward current
$I_F = f(T_A)$

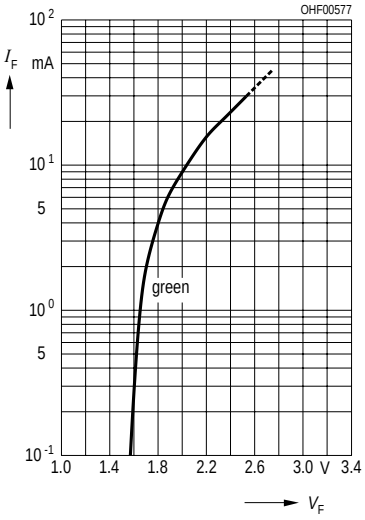


Relative spectral emission
$I_{rel} = f(\lambda)$

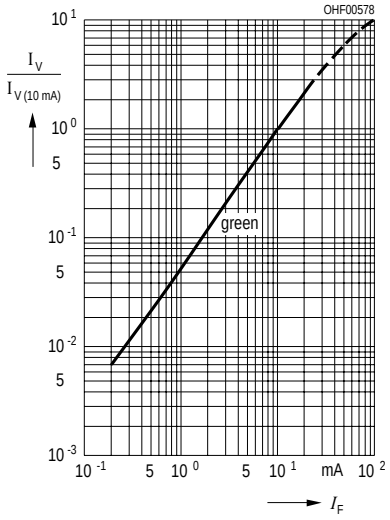


LED

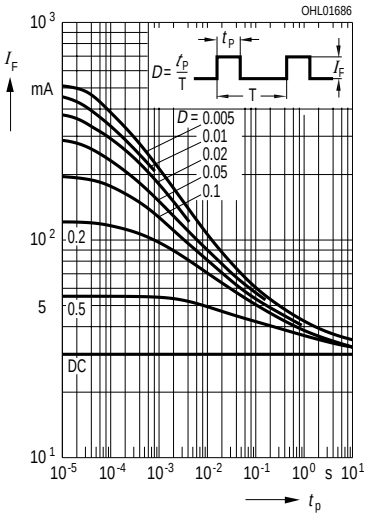
Forward current $I_F = f(V_F)$
T_A = 25 ˚C



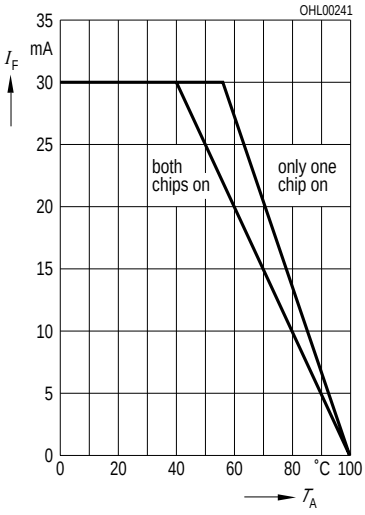
Relative luminous intensity
$I_V / I_{V(10\ mA)} = f(I_F)$, T_A = 25 ˚C



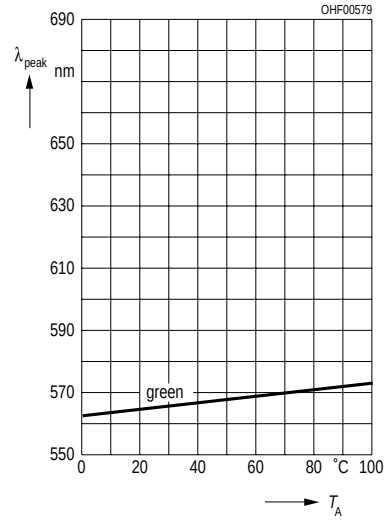
Perm. pulse handling capability $I_F = f(t_p)$
Duty cycle D = parameter, T_A = 25 ˚C



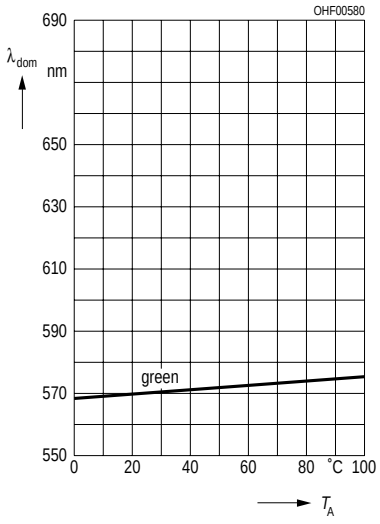
Max. permissible forward current
$I_F = f(T_A)$



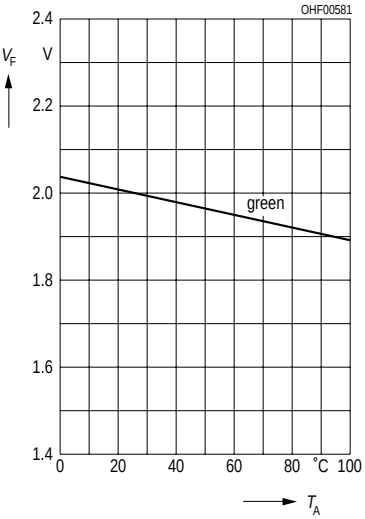
Wavelength at peak emission
$\lambda_{peak} = f(T_A)$, I_F = 10 mA



Dominant wavelength
$\lambda_{dom} = f(T_A)$, I_F = 10 mA



Forward voltage $V_F = f(T_A)$
$I_F = f(T_A)$



Relative luminous intensity
$I_V / I_{V(25\ ˚C)} = f(I_F)$, I_F = 10 mA